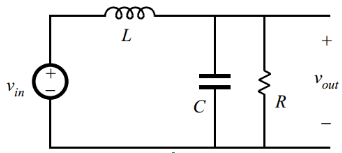
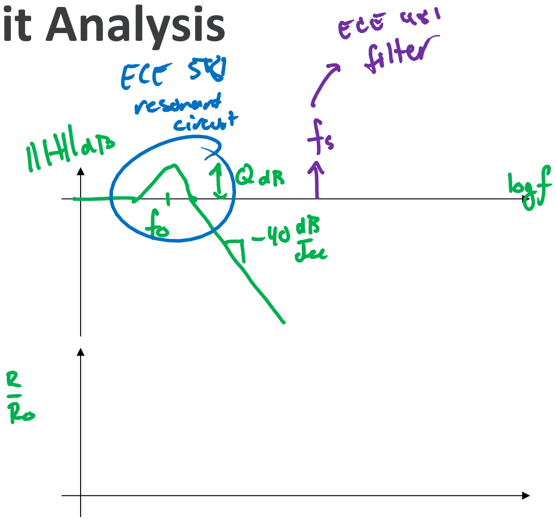
Resonant Circuit Analysis



$H(s) = \frac{1}{s^2LC + \frac{L}{R}s + 1}$

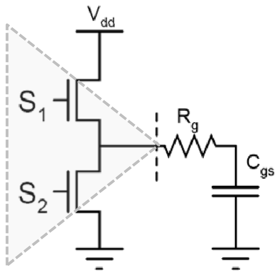
$\omega_0 = \frac{1}{\sqrt{LC}}$ $R_0 = \sqrt{\frac{L}{C}}$ $Q = \frac{R}{R_0}$

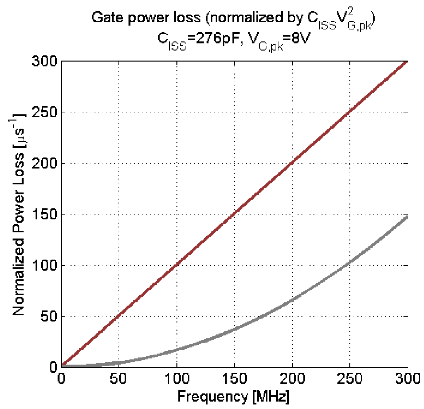


Soft Switching

- Advantages
  - Reduced switching loss
  - Possible operation at higher switching frequency
  - Lower EMI
- Disadvantages
  - Increased current and/or voltage stresses due to circulating current
  - Higher peak and rms current values
  - Complexity of analysis and modeling

Limitations: Gate Drive





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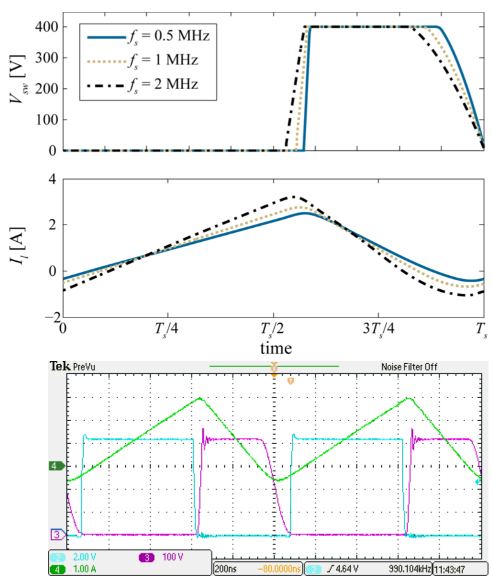
Limitations: t_d/T_s



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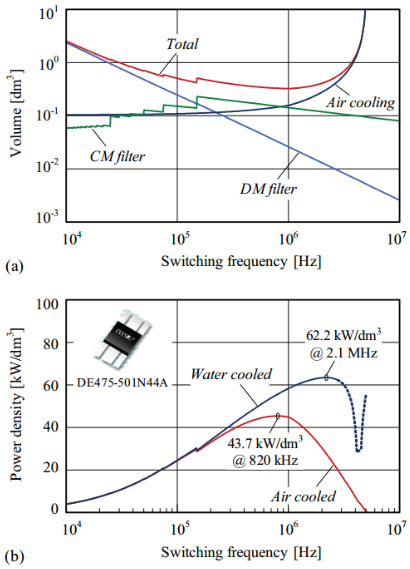
Limitations: Thermal



Kolar, J.W.; Drofenik, U.; Biela, J.; Heldwein, M.L.; Ertl, H.; Friedli, T.; Round, S.D., "PWM Converter Power Density Barriers," *Power Conversion Conference - Nagoya, 2007. PCC '07* , vol., no., pp.P-9,P-29, 2-5 April 2007

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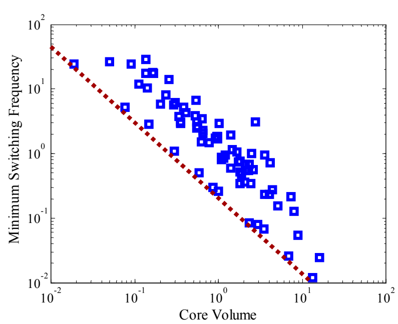
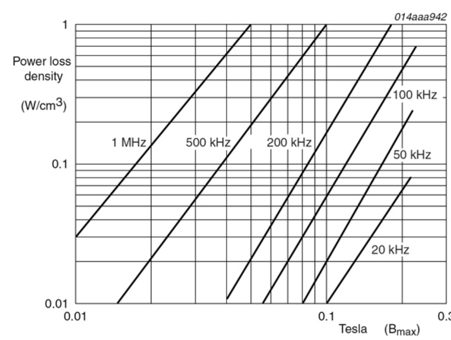
Limitations: Magnetics Design





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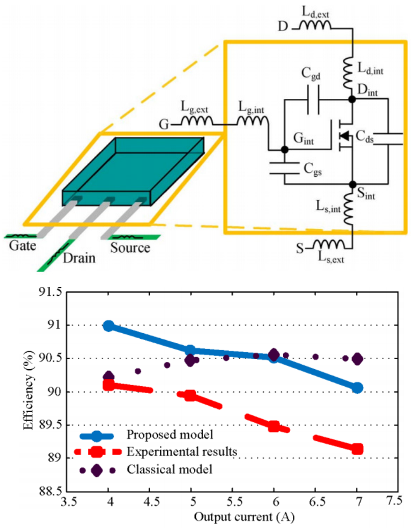
Limitations: Circuit Modeling



Rodríguez, M.; Rodríguez, A; Miaja, P.F.; Lamar, D.G.; Zúniga, J.S., "An Insight into the Switching Process of Power MOSFETs: An Improved Analytical Losses Model," *Power Electronics, IEEE Transactions on* , vol.25, no.6, pp.1626,1640, June 2010

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150-to-400V, 150W Boost

EXPERIMENTAL EXAMPLE

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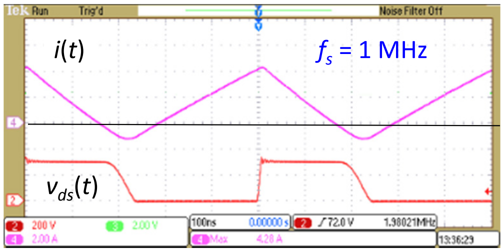
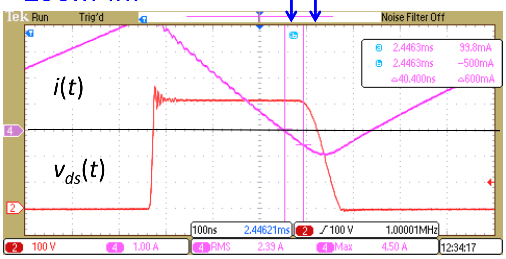
ZVS with Si diode



Zoom-in:



- ZVS turn-ON
  - Eliminated losses due to C_{sw} discharge during turn-ON transient
  - Eliminated losses due to MOSFET di_F/dt during turn-ON transient
- Diode reverse recovery still impacts the waveforms and losses
- Increased current ripple
  - Increased conduction losses (by >30%)
  - Increased dv_{ds}/dt upon turn-OFF, MOSFET turn-OFF speed is more important

D. Costinett, D. Maksimovic, R. Zane, A. Rodríguez and A. Vázquez, "Comparison of reverse recovery behavior of silicon and wide bandgap diodes in high frequency power converters"

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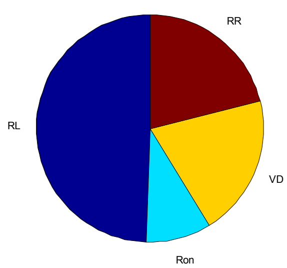
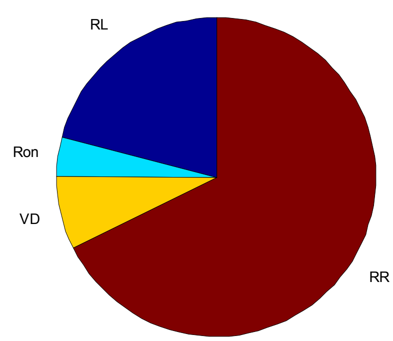
Loss Breakdown: Soft-Switched Si Boost

f_s = 100 kHz
P_{loss} = 5.7 W, η = 98.1%



Reverse-recovery:
21% of the total loss

f_s = 1 MHz
P_{loss} = 17.7 W, η = 94.4 %
Experiment: η = 95.1 %



Reverse-recovery:
68% of the total loss

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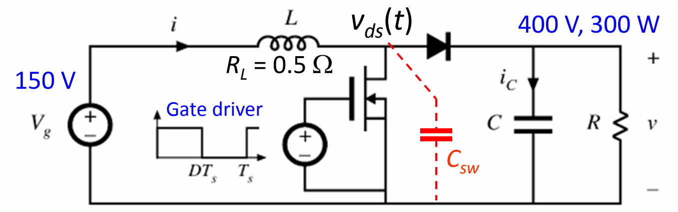
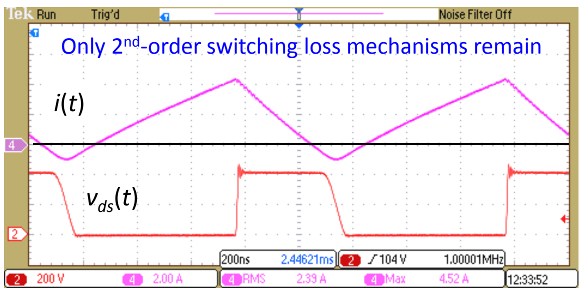
Soft-switched SiC diode



SiC diode, "soft-switched" operation



f_s = 1 MHz

MOSFET

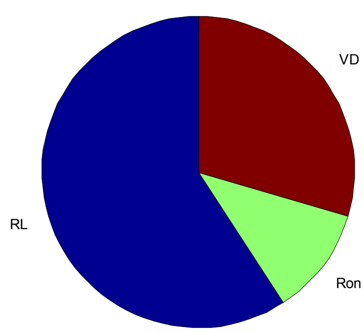
- di_F/dt = 200 A/μs
- $C_{ds,eq}$ = 45 pF
- R_{on} = 0.15 Ω

SiC diode

- t_{rr} = 0, Q_{rr} = 0
- $2C_{d,Qeq}$-$C_{d,eq}$ = 64 pF
- V_D = 1.8 V

Soft-switched Boost with SiC diode

Conduction losses only, 2nd-order switching losses not included in the model



100 kHz or 1 MHz
98.5% efficiency
P_{loss} = 4.5 W

Experiments:

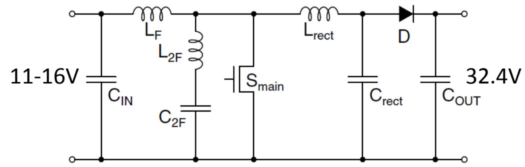
98.7% at 1 MHz
98.0% at 2 MHz

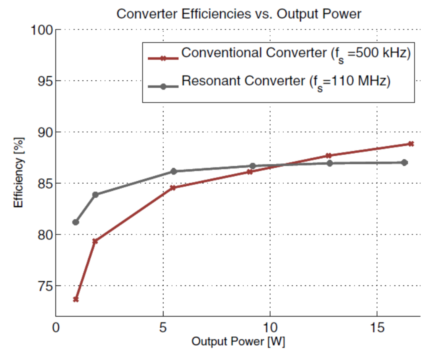
Power supply technology limits become dominated by:

- Magnetics
- 2nd-order switching loss mechanisms, e.g. gate-drive losses, parasitic inductances (layout and packaging)
- Gate-drive circuitry and controllers to support high-frequency operation

VHF power electronics [11]

Resonant Design		
Component	Value	Type
L_F	33 nH	Coilcraft 1812SMS
L_{2F}	12.5 nH	Coilcraft A04TG
L_{rect}	22 nH	1812SMS
C_{2F}	39 pF	ATC100A
C_{rect}	10 pF	ATC100A
C_{out}	75 μF	Multilayer Ceramics
C_{in}	22 μF	Multilayer Ceramics
S_{main}		Freescale MRF6S9060
D		Fairchild S310
Conventional Design		
Component	Value	Type
L_{boost}	10 μH	Coilcraft D03316T-103ML
C_{out}	75 μF	Multilayer Ceramics
C_{in}	22 μF	Multilayer Ceramics
S_{main}		LT1371HV
D		Fairchild S310





[11] D.J. Perreault, et..al. "Opportunities and challenges in very high frequency power conversion," IEEE APEC 2009.

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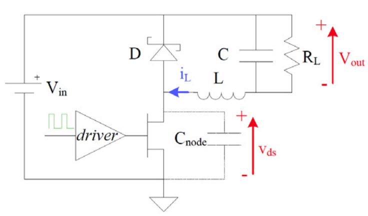
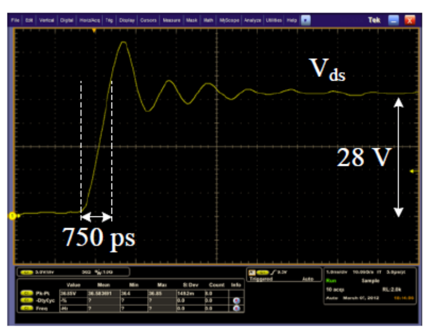
WBG Devices



TriQuint TGF2023-02
12W, DC-to-18 GHz
RF/microwave HEMT

FOM for switching applications
$C_{ds}R_{on} \approx 1\ \Omega$pF
$Q_gR_{on} \approx 10\ \Omega$pC

Standard hard-switched PWM operation at 50 MHz
dv_{ds}/dt dominated by probe (4 pF) capacitance



Emerging GaN HEMT devices may enable completely new RF-based design approaches in power electronics

M. Rodríguez, G. Stahl, D. Costinett and D. Maksimović, "Simulation and characterization of GaN HEMT in high-frequency switched-mode power converters,"

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Topics Covered

- **Course Topics**
  - High Frequency Power Conversion
    - Switching losses and device selection
    - Resonance in power electronics
    - Soft switching (ZVS and ZCS)
    - Magnetics design
  - Non-resonant soft switching converters
    - Constant frequency control
    - State-plane analysis
    - Resonant switches
    - Modeling and Simulation
    - Discrete time models
  - Resonant Converters
    - Resonant converter topologies
    - Sinusoidal analysis
    - AC-modeling and frequency modulation
    - State-plane analysis
  - Applications and practical issues of high frequency converters

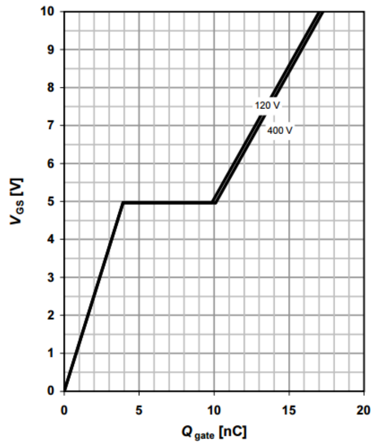
HARD SWITCHING ANALYSIS

Gate Charge

9 Typ. gate charge

V_{GS}=f(Q_{gate}); I_D=5.2 A pulsed

parameter: V_{DD}



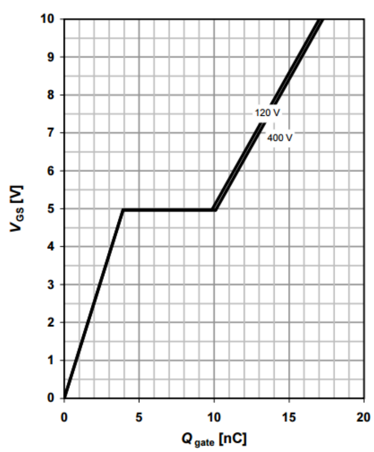
Overlap Time

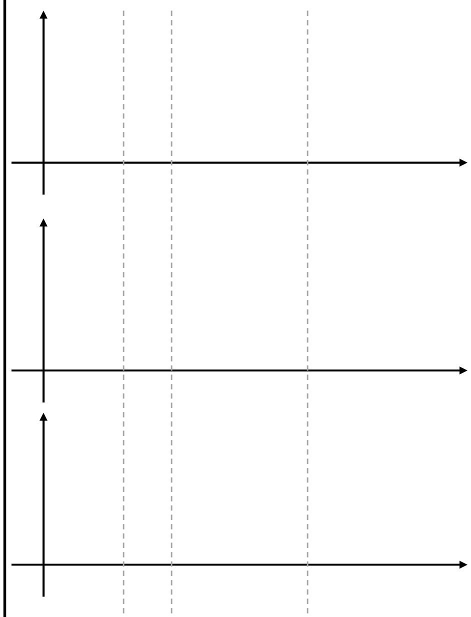
9 Typ. gate charge

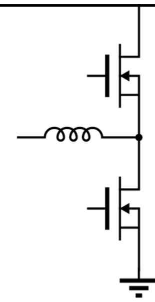
V_{GS}=f(Q_{gate}); I_D=5.2 A pulsed

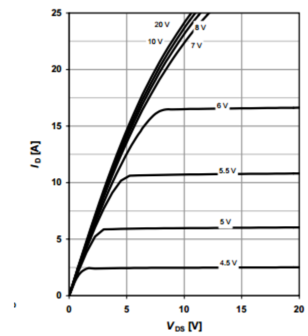
parameter: V_{DD}

Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=0.34 mA	2.5	3	3.5	
Gate resistance	R_G	f=1 MHz, open drain	-	1.8	-	Ω








25
20
15
10
5
0
20 V
10 V
8 V
7 V
6 V
5.5 V
5 V
4.5 V
I_D [A]
0
5
10
15
20
V_{DS} [V]